2SA1785 : PNP Epitaxial Planar Silicon Transistor 2SC4645 : NPN Triple Diffused Planar Silicon Transistor



2SA1785/2SC4645

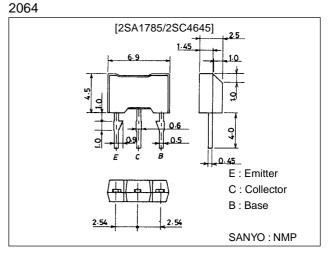
# **High Voltage Driver Applications**

### Features

- · Large current capacity ( $I_C=1A$ ).
- · High breakdown voltage (V<sub>CEO</sub> $\geq$ 400V).

### **Package Dimensions**

unit:mm



():2SA1785

## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)400	V
Collector-to-Emitter Voltage	VCEO		(-)400	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		()5	V
Collector Current	۱ <sub>C</sub>		()1	A
Colletor Current (Pulse)	ICP		(–)2	A
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)300V, I <sub>E</sub> =0			(–)1.0	μA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)1.0	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)100mA	40*		200*	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		(50)70		MHz
Output Capacitance	Cob	V <sub>CB</sub> =(-)30V, f=1MHz		(12)8		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)200mA, I <sub>B</sub> =(-)20mA			(–)1.0	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)200mA, I <sub>B</sub> =(-)20mA			(–)1.0	V

 $\ast$  : The 2SA1785/2SC4465 are classified by 100mA  $h_{FE}$  as follows :

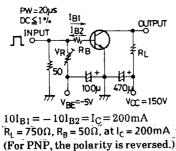
40 C 80 60 D 120 100 E 200

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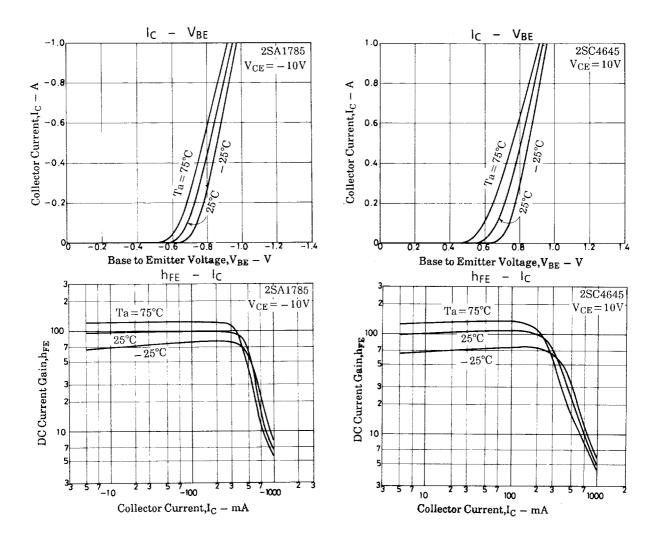
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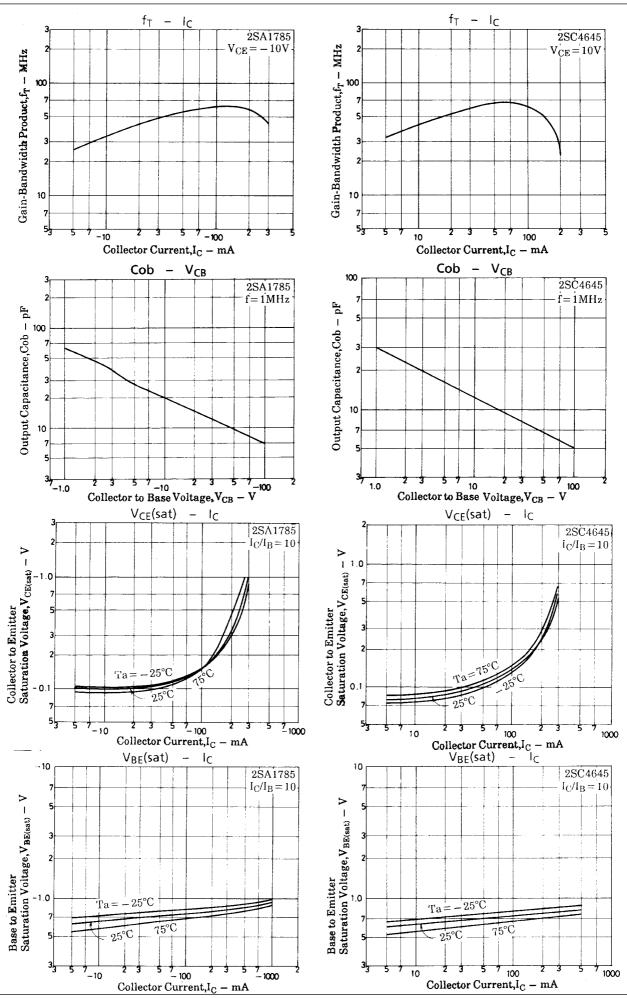
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10µA, I <sub>E</sub> =0	(–)400			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(–)400			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0	(–)5			V
Turn-ON Time	ton	See specified Test Circuit		(0.25)		μs
				0.11		μs
Storage Time	tstg	See specified Test Circuit		(3.0)		μs
				4.0		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit		(0.3)		μs
				0.65		μs

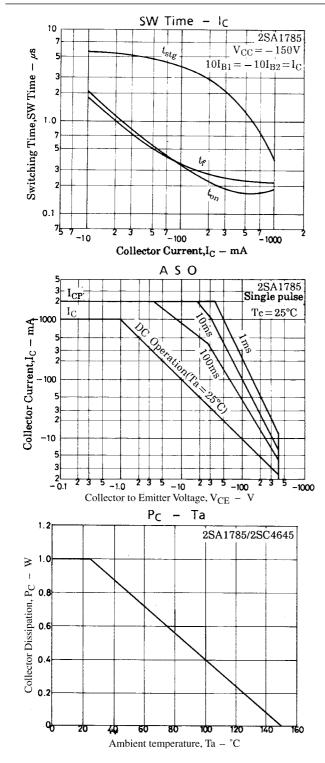
#### **Switching Time Test Circuit**

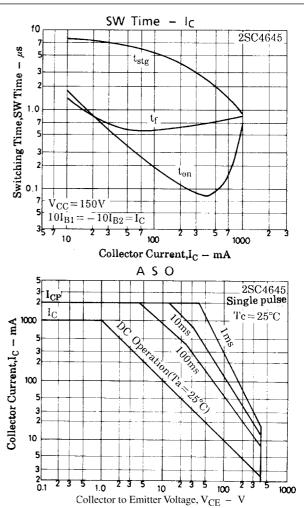


(For PNP, the polarity is reversed.) Unit (resistance :  $\Omega$ , capacitance : F)









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